



Attorney Docket, SEL 123

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In Re Application of )  
)  
Akiharu MIYANAGA et al. )  
)  
Serial No.: 09/241,695 )  
)  
Filed: February 2, 1999 )  
)  
For: Semiconductor Device And )  
Process For Producing The Same )  
)  
Art Unit: 2811 )  
)  
Examiner: S. Hu )

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231 on October 24, 2001

Signature *BR.*

Date 10/24/01

Commissioner for Patents  
Washington, D.C. 20231

**AMENDMENT AFTER FINAL**

Please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please cancel claim 49. ✓

Please amend claims 1, 27-29, 34, 42 and 48 as follows:

1. (Amended) A semiconductor device comprising a plurality of MOSFETs formed in a single crystal semiconductor substrate,
- each of the plurality of MOSFETs comprising:
- a source region and a drain region each including a first impurity;
- a channel forming region being formed between the source region and the drain region; and

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